Fangzhen Wu

List of Publications by Year
in descending order

12 papers	117 citations	1478458 6 h-index	1372553 10 g-index
13 all docs	13 docs citations	13 times ranked	95 citing authors

#	Article	IF	Citations
1	Direct Determination of Burgers Vectors of Threading Mixed Dislocations in 4H-SiC Grown by PVT Method. Journal of Electronic Materials, 2016, 45, 2045-2050.	2.2	15
2	Synchrotron X-ray topographic study on nature of threading mixed dislocations in 4Hâ€“SiC crystals grown by PVT method. Journal of Crystal Growth, 2016, 452, 39-43.	1.5	6
3	Characterization of V-shaped Defects in 4H-SiC Homoepitaxial Layers. Journal of Electronic Materials, 2015, 44, 1293-1299.	2.2	4
4	Direct Determination of Burgers Vectors of Threading Mixed Dislocations in 4H-SiC c-Plane Wafers Grown by PVT Method. ECS Transactions, 2015, 69, 33-38.	0.5	1
5	Direct Observation of Stacking Fault Nucleation from Deflected Threading Dislocations with Burgers Vector c+a in PVT Grown 4H-SiC. Materials Research Society Symposia Proceedings, 2014, 1693, 49.	0.1	3
6	A method to determine fault vectors in 4H-SiC from stacking sequences observed on high resolution transmission electron microscopy images. Journal of Applied Physics, 2014, 116, 104905.	2.5	2
7	Characterization of Threading Dislocations in PVT-Grown AlN Substrates via x-Ray Topography and Ray Tracing Simulation. Journal of Electronic Materials, 2014, 43, 838-842.	2.2	29
8	Characterization and Formation Mechanism of Six Pointed Star-Type Stacking Faults in 4H-SiC. Journal of Electronic Materials, 2013, 42, 787-793.	2.2	3
9	Quantitative Comparison Between Dislocation Densities in Offcut 4H-SiC Wafers Measured Using Synchrotron X-ray Topography and Molten KOH Etching. Journal of Electronic Materials, 2013, 42, 794-798.	2.2	5
10	Grazing Incidence X-ray Topographic Studies of Threading Dislocations in Hydrothermal Grown ZnO Single Crystal Substrates. Materials Research Society Symposia Proceedings, 2013, 1494, 121-126.	0.1	7
11	Simulation of Grazing-Incidence Synchrotron X-ray Topographic Images of Threading c+a Dislocations in 4H-SiC. Materials Research Society Symposia Proceedings, 2012, 1433, 53.	0.1	23
12	Analysis of Dislocation Behavior in Low Dislocation Density, PVT-Grown, Four-Inch Silicon Carbide Single Crystals. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	18